

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : An L. STEEGEN et al.

Confirmation No. 2905

Appln. No. : 10/605,906

Group Art Unit: 2813

Filed : November 5, 2003

Examiner: Stephen W. Smoot

For : METHOD AND STRUCTURE FOR FORMING STRAINED SI FOR  
CMOS DEVICES

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
U.S. Patent and Trademark Office  
Customer Service Window, Mail Stop Amendment  
Randolph Building  
401 Dulany Street  
Alexandria VA 22314

Sir :

In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and supplemental to the Information Disclosure Statements filed on November 5, 2003, August 23, 2005 and February 9, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned. Copies of the non-US patent documents as well as the documents listed in the "Other Documents" section of the attached PTO-1449 are enclosed.

Applicant respectfully requests that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that this Information Disclosure Statement is being after receipt of a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, Applicants are herein submitting the required fee, and authorization is hereby given to charge Deposit Account No. 09-0458 any fee necessary to ensure consideration of these materials.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,  
An L. STEEGEN et al.

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', written over a horizontal line.

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June 29, 2006  
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FORM PTO-1449

U.S. Department of Commerce  
Patent and Trademark OfficeAtty. Docket No.  
FIS920030236US1Application No.  
10/605,906INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT  
(Use several sheets if necessary)Applicant  
An L. STEEGEN et al.Filing Date  
11/05/2003Group  
2813

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan			X

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.	Application No.		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)				Applicant			
				Filing Date		Group	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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EXAMINER				DATE CONSIDERED			
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